

R-C Thermal Model Parameters

DESCRIPTION

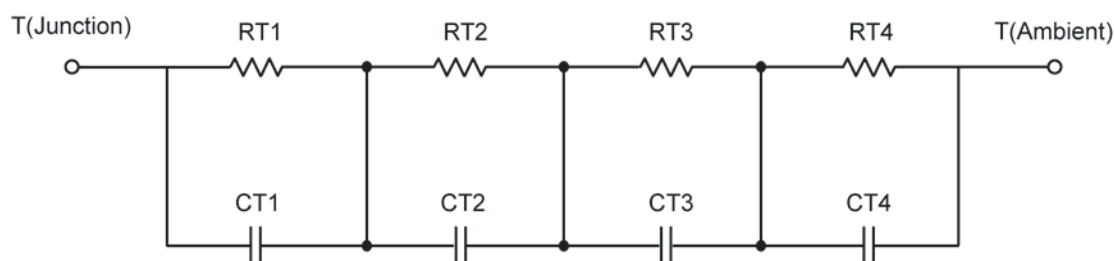
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

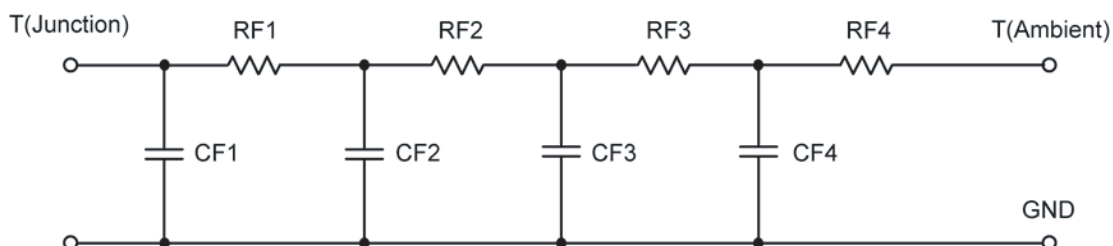
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	15.5802	N/A	13.9391
RT2	10.6052	N/A	15.2004
RT3	28.3155	N/A	6.4998
RT4	55.4991	N/A	5.3607
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	95.2581 m	N/A	3.2745 m
CT2	492.8587 u	N/A	8.1987 m
CT3	5.7462 m	N/A	240.8130 m
CT4	1.5858	N/A	322.0731 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	12.6722	N/A	6.3184
RF2	30.6842	N/A	17.7356
RF3	15.3329	N/A	11.3517
RF4	51.3107	N/A	5.5943
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	451.7455 u	N/A	279.0812 u
CF2	5.3255 m	N/A	1.7749 m
CF3	134.7193 m	N/A	5.5590 m
CF4	1.6811	N/A	262.0864 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

